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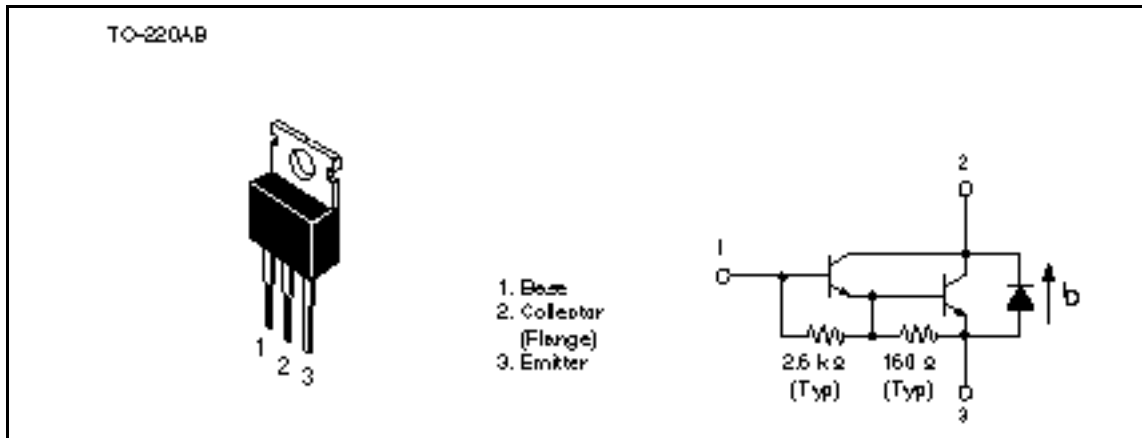
Silicon NPN Triple Diffused

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Application

Low frequency power amplifier

Outline



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	120	V
Collector to emitter voltage	V _{CEO}	120	V
Emitter to base voltage	V _{EBO}	7	V
Collector current	I _C	6	A
Collector peak current	I _{C(peak)}	12	A
Collector power dissipation	P _C ^{*1}	40	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C
C to E diode forward current	I _D ^{*1}	6	A

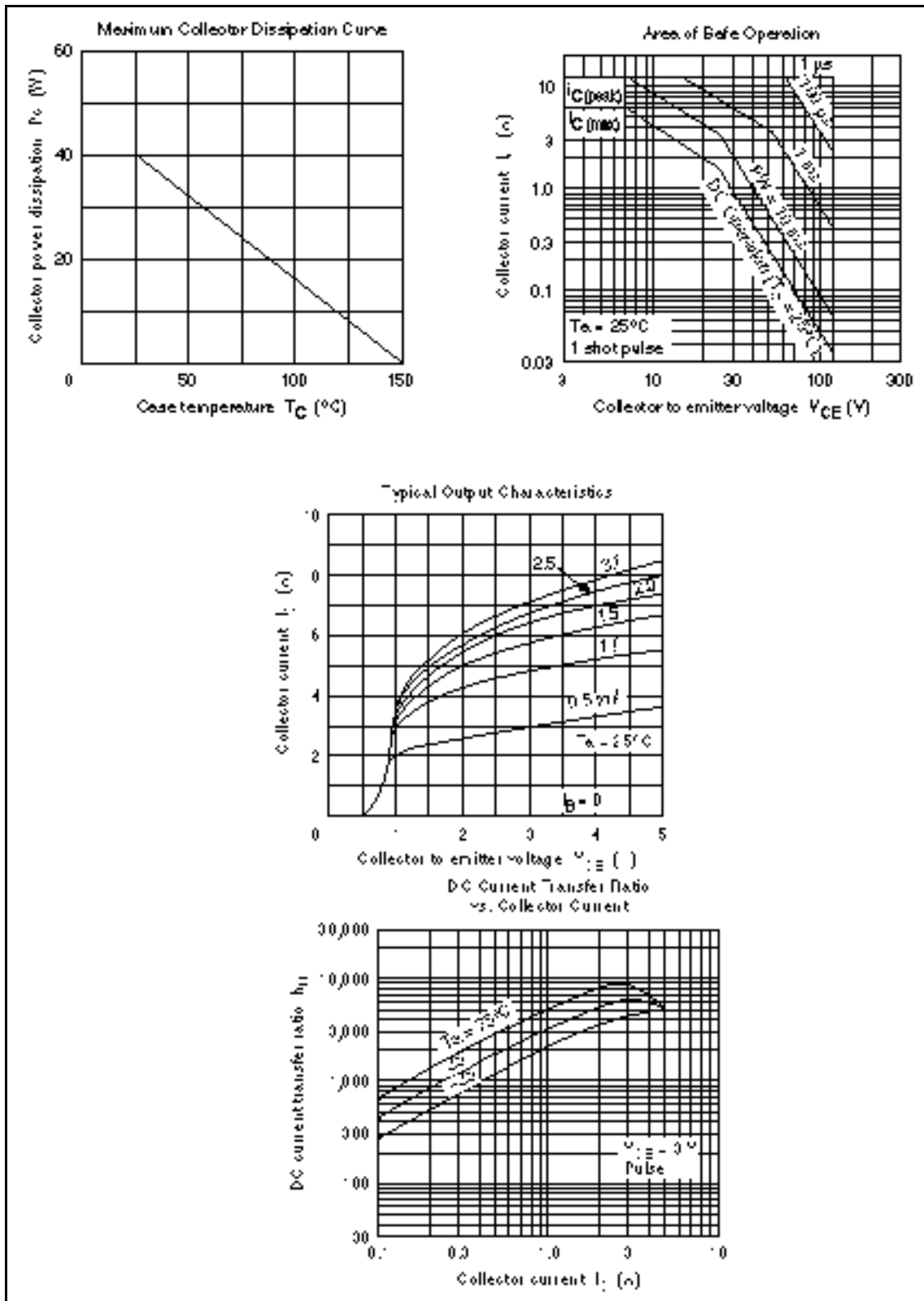
Note: 1. Value at T_c = 25°C.

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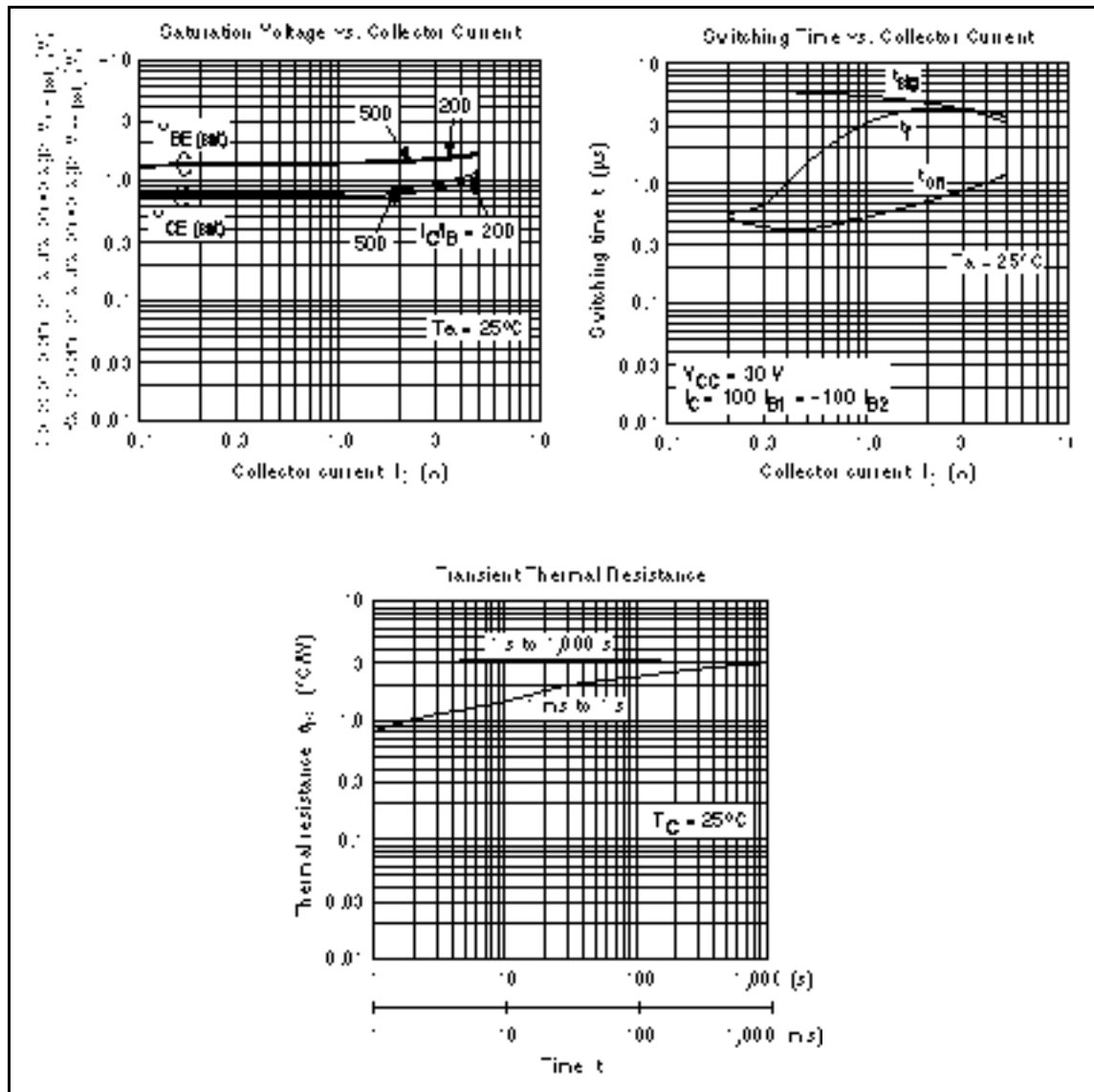
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	120	—	—	V	$I_C = 25 \text{ mA}, R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	7	—	—	V	$I_E = 50 \text{ mA}, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	100	μA	$V_{CB} = 120 \text{ V}, I_E = 0$
	I_{CEO}	—	—	10	μA	$V_{CE} = 100 \text{ V}, R_{BE} =$
DC current transfer ratio	h_{FE}	1000	—	20000		$V_{CE} = 3 \text{ V}, I_C = 3 \text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)1}$	—	—	1.5	V	$I_C = 3 \text{ A}, I_B = 6 \text{ mA}^{*1}$
	$V_{CE(sat)2}$	—	—	3.0	V	$I_C = 6 \text{ A}, I_B = 60 \text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)1}$	—	—	2.0	V	$I_C = 3 \text{ A}, I_B = 6 \text{ mA}^{*1}$
	$V_{BE(sat)2}$	—	—	3.5	V	$I_C = 6 \text{ A}, I_B = 60 \text{ mA}^{*1}$
C to E diode forward voltage	V_D	—	—	3.0	V	$I_D = 6 \text{ A}^{*1}$
Turn on time	t_{on}	—	0.6	—	μs	$I_C = 3 \text{ A}, I_{B1} = -I_{B2} = 6 \text{ mA}$
Storage time	t_{stg}	—	7.0	—	μs	
Fall time	t_f	—	2.0	—	μs	

Note: 1. Pulse test.



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